MOSFET Silicon N-Channel MOS

1. Applications

Boost PFC switch,single-ended flyback or two-transistor forward topologies.
PC power, PD Adaptor,LCD & PDP TV and LED lighting.

2. Features

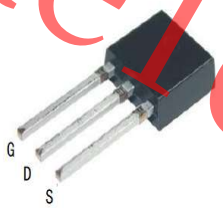
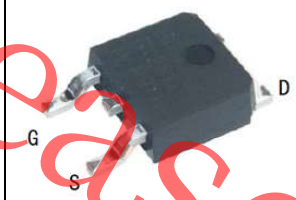
Low drain-source on-resistance: RDS(ON) = 0.750Ω (typ.)
Easy to control Gate switching
Enhancement mo de: Vth = 2.8 to 4.2 V

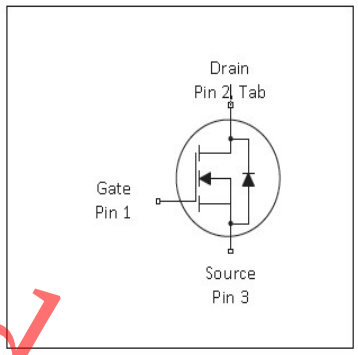
Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	700	V
$R_{DS(on),max}$	850	m Ω
$Q_{g,typ}$	10.3	nC
$I_{D,pulse}$	18	A

3. Packaging and Internal Circuit

Part Name	Package	Marking
ASA65R850E	TO220F	ASA65R850E
ASU65R850E	TO251	ASU65R850E
ASD65R850E	TO252	ASD65R850E

TO220F	TO251	TO252
		



1 Maximum ratings

at T_j = 25°C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D		-	6	A	T_C=25°C
Pulsed drain current[2]	$I_{D,pulse}$	-	-	18	A	T_C=25°C
Avalanche energy, single pulse	E_{AS}	-	-	624	mJ	
MOSFET dv/dt ruggedness	dv/dt	-	-	36	V/ns	V_{DS}=0...400V
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC (f>1 Hz)
Power dissipation (TO220F)	P_{tot}	-	-	27	W	T_C=25°C
Power dissipation (TO252&TO251)	P_{tot}	-	-	74	W	T_C=25°C
Storage temperature	T_{stg}	-55	-	150	°C	
Operating junction temperature	T_j	-55	-	150	°C	
Reverse diode dv/dt[3]	dv/dt	-	-	15	V/ns	V_{DS}=0...400V, I_{SD}<=48A, T_j=25°C see table 8

[1] Limited by $T_{j,max}$. Maximum Duty Cycle D = 0.50
[2] Pulse width t_p limited by $T_{j,max}$
[3] Identical low side and high side switch with identical R_G

2 Thermal characteristics

Table 3 Thermalcharacteristics (TO220 FullPAK)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	4.6	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	80	°C/W	device on PCB, minimal footprint

Thermalcharacteristics (TO251 and TO252)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.7	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint

3 Electrical characteristics

at T_j=25°C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	655	-	-	V	V_{GS}=0V, I_D=10mA
Gate threshold voltage	$V_{(GS)th}$	2.8		4.2	V	V_{DS}=V_{GS}, I_D=250uA
Zero gate voltage drain current	I_{DSS}	-	-	100	nA	V_{DS}=650V, V_{GS}=0V, T_j=25°C
Gate-source leakage current	I_{GSS}	-	-	100	nA	V_{GS}=30V, V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	0.75	0.85	Ω	V_{GS}=10V, I_D=2.5A, T_j=25°C
Gate resistance	R_G	-	33.7	-		f=1MHz, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	377	-	pF	V_{GS}=0V, V_{DS}=50V, f=10kHz
Output capacitance	C_{oss}	-	33	-	pF	V_{GS}=0V, V_{DS}=50V, f=10kHz
Reverse transfer capacitance	C_{rss}	-	4.55	-	pF	V_{GS}=0V, V_{DS}=50V, f=10kHz
Turn-on delay time	$t_{d(on)}$	-	8.4	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=2.5A, R_G=6.8Ω; see table 9
Rise time	t_r	-	21.6	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=2.5A, R_G=6.8Ω; see table 9
Turn-off delay time	$t_{d(off)}$	-	45.2	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=2.5A, R_G=6.8Ω; see table 9
Fall time	t_f	-	24.4	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=2.5A, R_G=6.8Ω; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	1.845	-	nC	V_{DD}=400V, I_D=2.5A, V_{GS}=0 to 10V
Gate to drain charge	Q_{gd}	-	2.723	-	nC	V_{DD}=400V, I_D=2.5A, V_{GS}=0 to 10V
Gate charge total	Q_g	-	10.3	-	nC	V_{DD}=400V, I_D=2.5A, V_{GS}=0 to 10V
Gate plateau voltage	$V_{plateau}$	-	6.4	-	V	V_{DD}=400V, I_D=2.5A, V_{GS}=0 to 10V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.78	-	V	V_{GS}=0V, I_F=1A, T_j=25°C
Reverse recovery time	t_{rr}	-	124	-	ns	V_R=400V, I_F=2.5 A, di_F/dt=100A/µs; see table 8
Reverse recovery charge	Q_{rr}	-	0.88	-	uC	V_R=400V, I_F=2.5 A, di_F/dt=100A/µs; see table 8
Peak reverse recovery current	I_{rrm}	-	10	-	A	V_R=400V, I_F=2.5 A, di_F/dt=100A/µs; see table 8

4 Test Circuits

Table 8 Diode characteristics

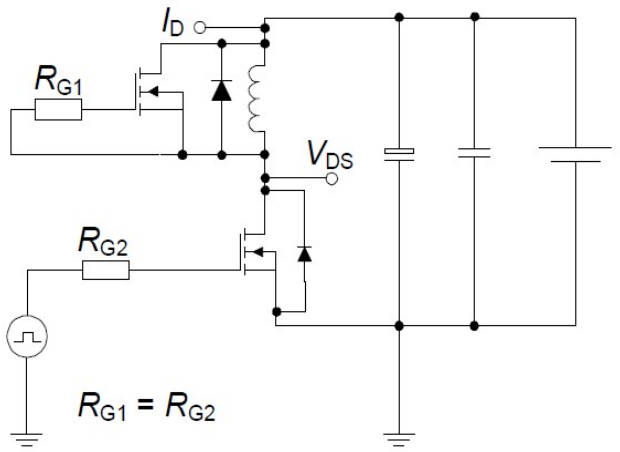
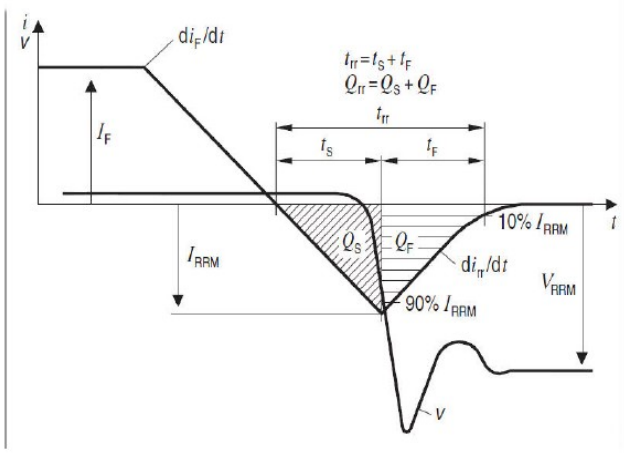
Test circuit for diode characteristics	Diode recovery waveform
	

Table 9 Switching times

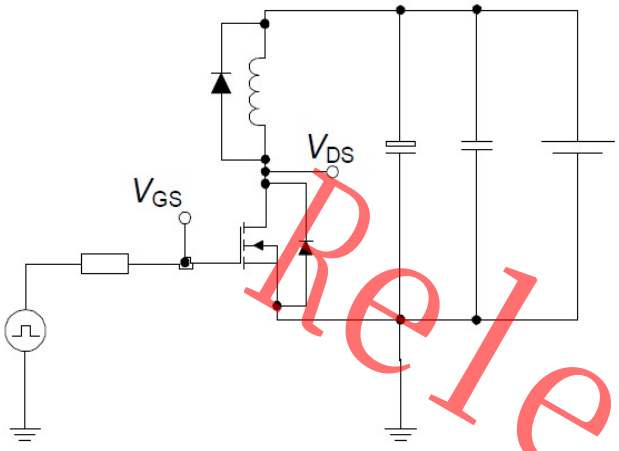
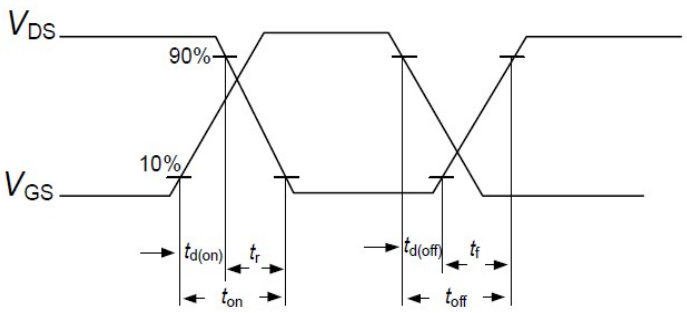
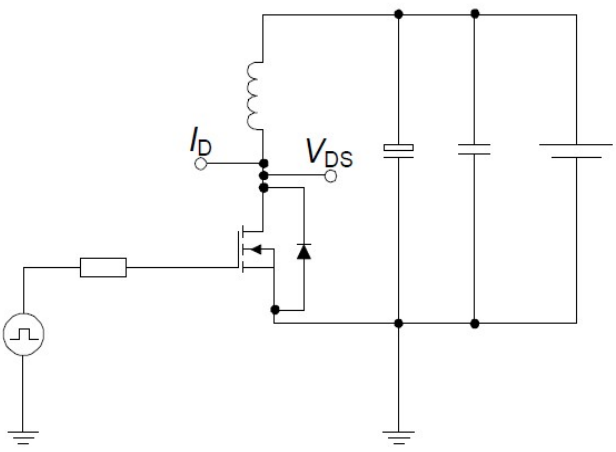
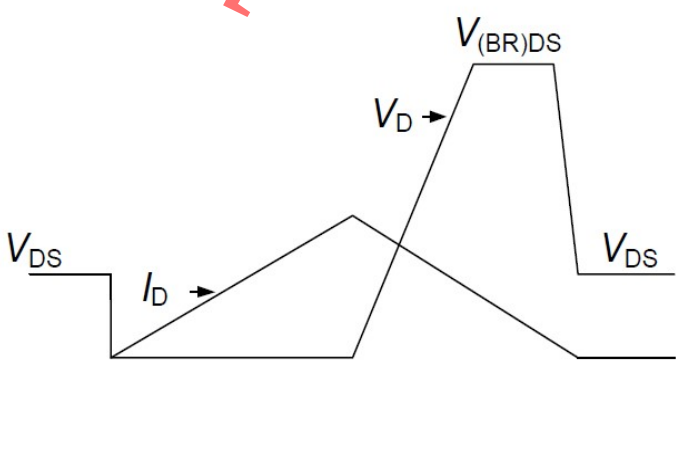
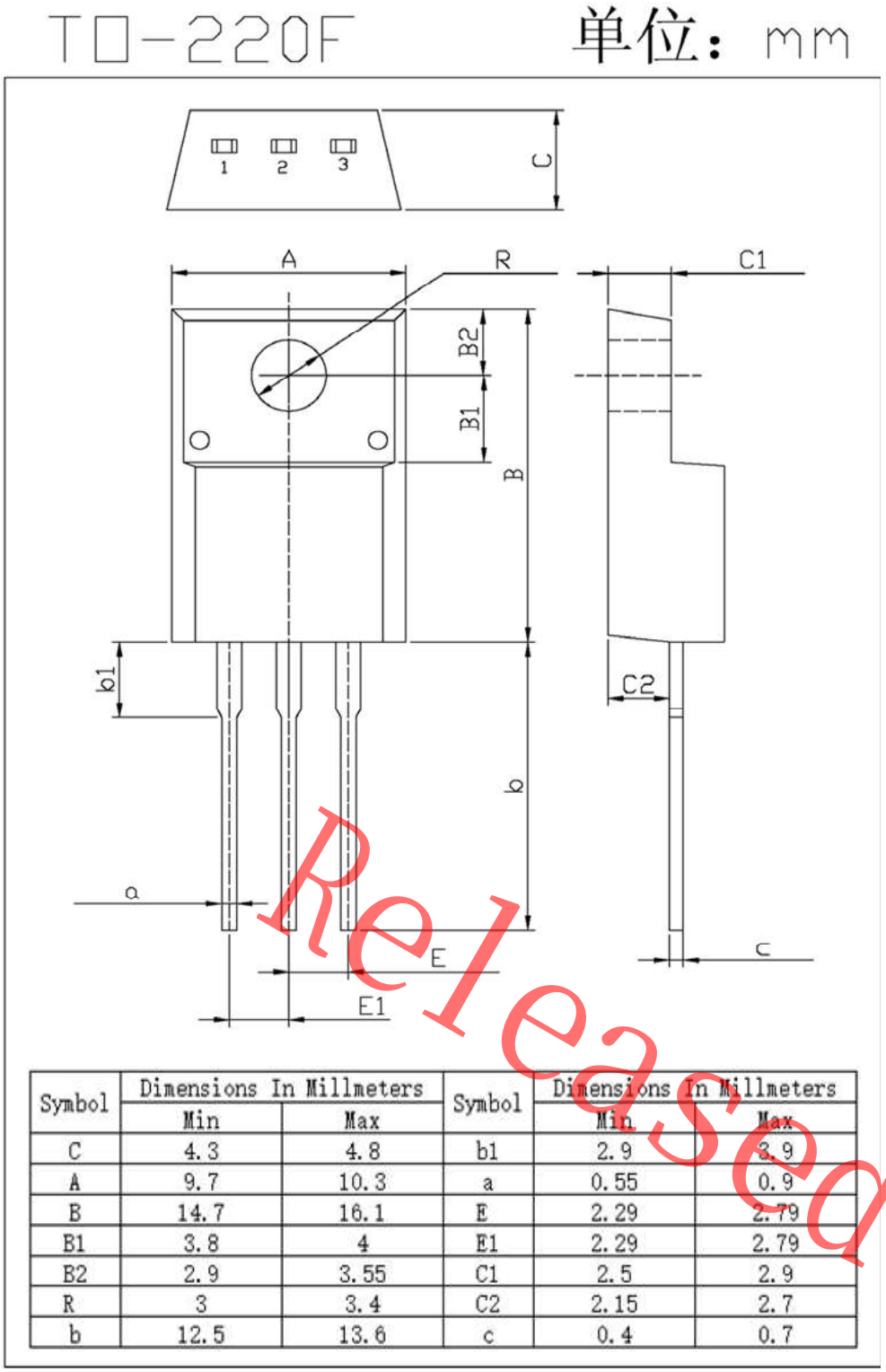
Switching times test circuit for inductive load	Switching times waveform
	

Table10 Unclamped inductive load

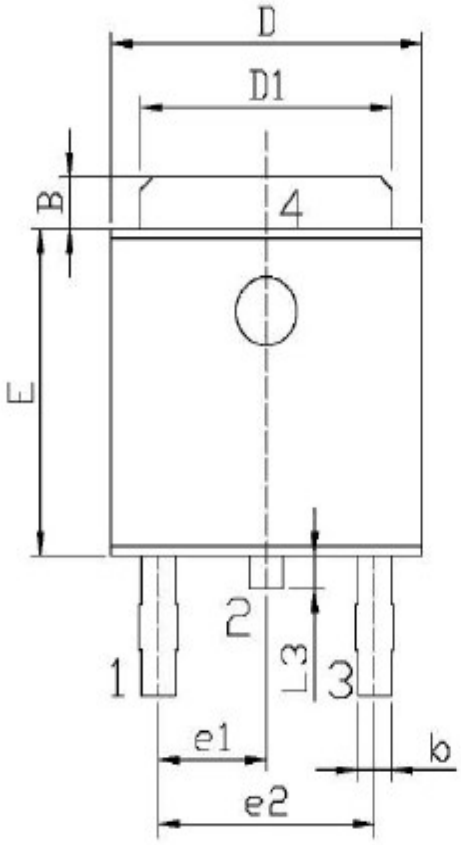
Unclamped inductive load test circuit	Unclamped inductive waveform
	

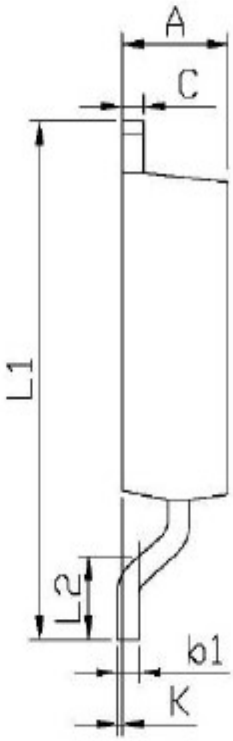
5 Package Outlines



Symbol	Dimensions In Millmeters		Symbol	Dimensions In Millmeters	
	Min	Max		Min	Max
C	4.3	4.8	b1	2.9	3.9
A	9.7	10.3	a	0.55	0.9
B	14.7	16.1	E	2.29	2.79
B1	3.8	4	E1	2.29	2.79
B2	2.9	3.55	C1	2.5	2.9
R	3	3.4	C2	2.15	2.7
b	12.5	13.6	c	0.4	0.7

Figure1：Outline PG-TO220F

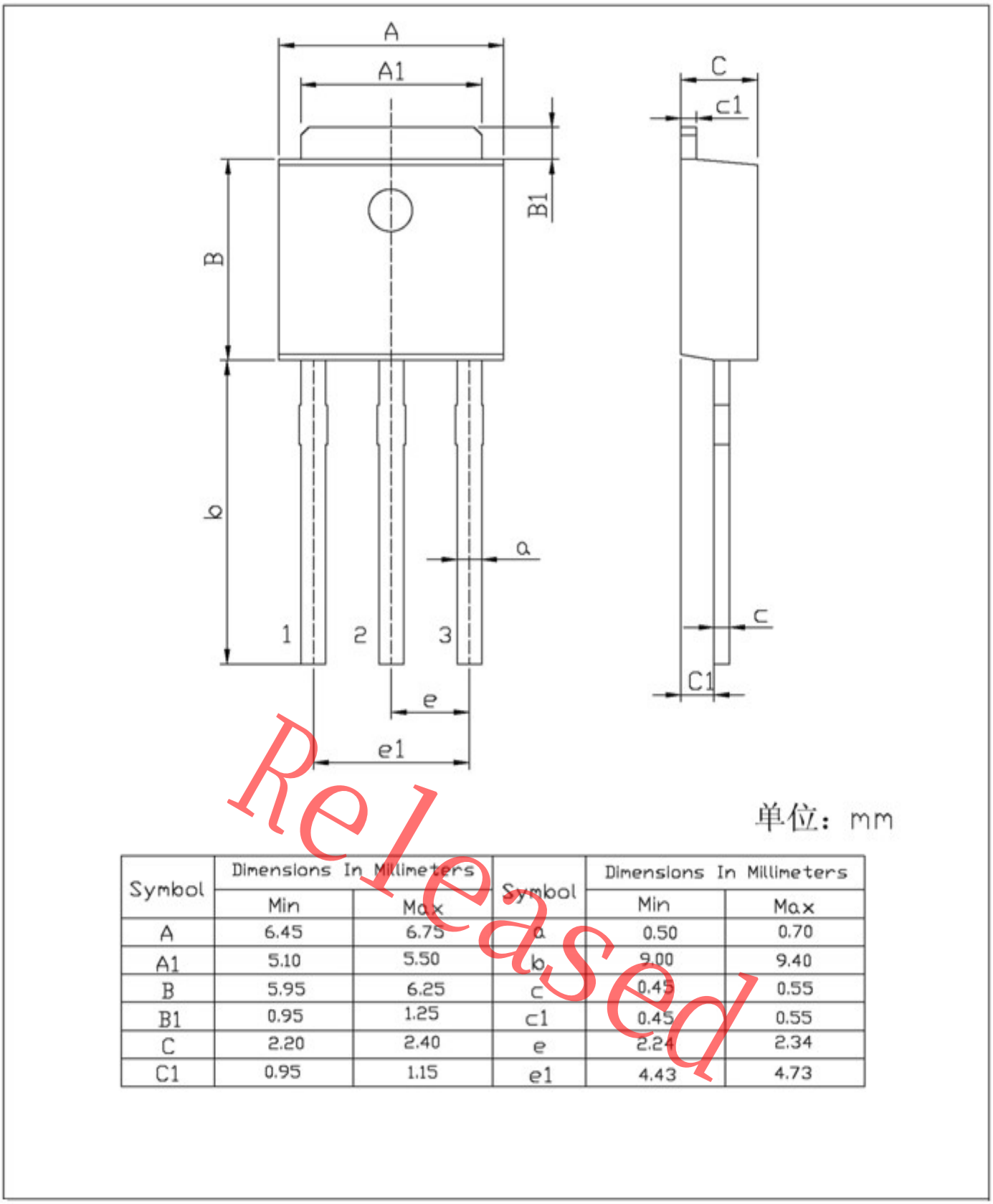




单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.70	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

Figure2：OutlinePG-TO252



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	6.45	6.75	a	0.50	0.70
A1	5.10	5.50	b	9.00	9.40
B	5.95	6.25	c	0.45	0.55
B1	0.95	1.25	c1	0.45	0.55
C	2.20	2.40	e	2.24	2.34
C1	0.95	1.15	e1	4.43	4.73

Figure3：OutlinePG-TO251

Revision History

ASA65R850E

Revision	Date	Subjects (major changes since last revision)
0.1	2019-04-11	Preliminary version
1.0	2019-11-07	Fine tune outline and add Crss test data.etc